

Intel, Micron Introduce 25-Nanometer NAND -- The Smallest, Most Advanced Process Technology in the Semiconductor Industry

World's First 25nm NAND Technology Provides Cost-Effective Path for More Data, Photos, Songs in Today's Popular Consumer Electronic and Computing Devices

NEWS HIGHLIGHTS

- -- Intel, Micron lead semiconductor industry with world's first 25nm process technology.
- -- New 25nm flash provides more cost-effective path to increase storage for portable music/media players, smartphones and solid-state drives.
- -- 25nm process produces 8 gigabytes (GB) of storage in a single NAND device, creating a high-capacity storage solution for consumer gadgets.

SANTA CLARA, Calif. and BOISE, Idaho, Feb. 1, 2010 (GLOBE NEWSWIRE) -- Intel Corporation and Micron Technology, Inc. (Nasdaq:MU) today announced the world's first 25-nanometer (nm) NAND technology, which provides a more cost-effective path for increasing storage capacity in such popular consumer gadgets as smartphones, personal music and media players (PMPs), as well as the new high-performance class of solid-state drives (SSDs).

NAND flash memory stores data and other media contained in consumer electronics products, retaining information even when the power is turned off. The drive toward smaller NAND processes enables the continued development and introduction of new uses for the technology. Not only is the 25nm process the smallest NAND technology, it is also the smallest semiconductor technology in the world -- a technological accomplishment that continues the advancement of more music, video, and other data in today's consumer electronics and computing applications.

Manufactured by IM Flash Technologies (IMFT), Intel and Micron's NAND flash joint venture, the 25nm process produces 8 gigabytes (GB) of storage in a single NAND device, creating a high-capacity storage solution for today's tiny consumer gadgets. It measures just 167mm2 - small enough to fit through the hole in the middle of a compact disc (CD), yet packs more than 10 times the data capacity of that CD (a standard CD holds 700 megabytes of data).

With a committed focus and investment in NAND research and development, Intel and Micron have doubled NAND density roughly every 18 months, which leads to smaller, more cost-efficient and higher capacity products. IMFT started production with a 50nm process in

2006, followed by a 34nm process in 2008. With today's 25nm process, the companies are extending their process and fabrication leadership further with the introduction of the smallest semiconductor lithography available in the industry.

"To lead the entire semiconductor industry with the most advanced process technology is a phenomenal feat for Intel and Micron, and we look forward to further pushing the scaling limits," said Brian Shirley, vice president of Micron's memory group. "This production technology will enable significant benefits to our customers through higher density media solutions."

"Through our continued investment in IMFT, we're delivering leadership technology and manufacturing that enable the most cost-effective and reliable NAND memory," said Tom Rampone, vice president and general manager, Intel NAND Solutions Group. "This will help speed the adoption of solid-state drive solutions for computing."

The 25nm, 8GB device is sampling now and is expected to enter mass production in the second quarter of 2010. For consumer electronics manufacturers, the device provides the highest-density in a single 2 bits-per-cell multi-level cell (MLC) die that will fit an industry-standard, thin small-outline package (TSOP). Multiple 8GB devices can be stacked in a package to increase storage capacity. The new 25nm 8GB device reduces chip count by 50 percent compared to previous process generations, allowing for smaller, yet higher density designs and greater cost efficiencies. For example, a 256GB solid-state drive (SSD) can now be enabled with just 32 of these devices (versus 64 previously), a 32GB smartphone needs just four, and a 16GB flash card requires only two.

Relevant Links

For up-to-date Micron and Intel news:

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-- Micron Innovations Blog: <a href="https://www.micronblogs.com">www.micronblogs.com</a>
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-- Micron on Twitter: http://twitter.com/microntechnews

-- Micron Pressroom: www.micron.com/media

-- Intel Pressroom: www.intel.com/pressroom

-- Intel Blog: http://blogs.intel.com

-- Intel on Twitter: http://twitter.com/intelnews

About Intel

Intel (Nasdaq:INTC), the world leader in silicon innovation, develops technologies, products and initiatives to continually advance how people work and live. Additional information about Intel is available at www.intel.com/pressroom and http://blogs.intel.com. For more details on Intel NAND flash solutions go to www.intel.com/go/ssd.

The Intel Corporation logo is available at https://www.globenewswire.com/newsroom/prs/? pkgid=7015

About Micron

Micron Technology, Inc., is one of the world's leading providers of advanced semiconductor solutions. Through its worldwide operations, Micron manufactures and markets DRAMs, NAND flash memory, other semiconductor components, and memory modules for use in leading-edge computing, consumer, networking, and mobile products. Micron's common stock is traded on the NASDAQ under the MU symbol. To learn more about Micron Technology, Inc., visit www.micron.com.

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This news release contains forward-looking statements regarding the production of the 25nm 8GB NAND device. Actual events or results may differ materially from those contained in the forward-looking statements. Please refer to the documents Micron files on a consolidated basis from time to time with the Securities and Exchange Commission, specifically Micron's most recent Form 10-K and Form 10-Q. These documents contain and identify important factors that could cause the actual results for Micron on a consolidated basis to differ materially from those contained in our forward-looking statements (see Certain Factors). Although we believe that the expectations reflected in the forward-looking statements are reasonable, we cannot guarantee future results, levels of activity, performance or achievements.

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